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SECRETARIAT

c/o Inter Group Corp.
 Toranomom Takagi Bldg.,
 1-7-2, Nishishimbashi, Minato-ku,
 Tokyo 105-0003, Japan
 Phone: +81-3-3597-1108
 Fax: +81-3-3597-1097
 E-mail: ssdm_secretariat@intergroup.co.jp

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